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APPLICATION NO.	F.	ILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/496,794	02/02/2000		John T. Moore	MICT-0005-D1-US 6700	
21906	7590	06/14/2006		EXAMINER	
TROP PRU	JNER & I	HU, PC	OWENS, DOUGLAS W		
1616 S. VOSS ROAD, SUITE 750 HOUSTON, TX 77057-2631			ART UNIT		PAPER NUMBER
				2011	

DATE MAILED: 06/14/2006

Please find below and/or attached an Office communication concerning this application or proceeding.

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	Application No.	Applicant(s)					
	09/496,794	MOORE ET AL.					
Office Action Summary	Examiner	Art Unit					
	Douglas W. Owens	2811					
The MAILING DATE of this communication appears on the cover sheet with the correspondence address Period for Reply							
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication. - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication. - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).							
Status							
1) Responsive to communication(s) filed on 05 Ju	une 2006.						
2a) This action is FINAL . 2b) ⊠ This	action is non-final.						
3) Since this application is in condition for allowa	nce except for formal matters, pro	secution as to the merits is					
closed in accordance with the practice under E	closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.						
Disposition of Claims							
4) Claim(s) 26-30 is/are pending in the applicatio	n.·	•					
4a) Of the above claim(s) is/are withdraw	4a) Of the above claim(s) is/are withdrawn from consideration.						
5) Claim(s) is/are allowed.	5) Claim(s) is/are allowed.						
6)⊠ Claim(s) <u>26-30</u> is/are rejected.							
7) Claim(s) is/are objected to.							
8) Claim(s) are subject to restriction and/o	r election requirement.	·					
Application Papers							
9) The specification is objected to by the Examine	er.						
10)☐ The drawing(s) filed on is/are: a)☐ acc	epted or b) \square objected to by the E	Examiner.					
Applicant may not request that any objection to the							
Replacement drawing sheet(s) including the correct							
11)☐ The oath or declaration is objected to by the Ex	kaminer. Note the attached Office	Action or form PTO-152.					
Priority under 35 U.S.C. § 119							
 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No. 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 							
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Attachment(s)							
1) Notice of References Cited (PTO-892) 4) Interview Summary (PTO-413) Paper No(s)/Mail Date							
2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date 6) Other:							

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DETAILED ACTION

Continued Examination Under 37 CFR 1.114

1. A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on June 5, 2006 has been entered.

Claim Rejections - 35 USC § 103

- 2. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 3. Claims 26 30 are rejected under 35 U.S.C. 103(a) as being unpatentable over US Patent No. 5,763,932 to Pan et al.

Regarding claim 1, Pan et al. teach a semiconductor structure (Figs. 13 and 14), comprising;

a support (42);

a first material (44) deposited on said support, said first material being a dielectric (Col. 4, lines 17 – 27) having a first etch rate;

a trench formed through said first material and into the support (Fig. 10); and

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a trench filler material (74) deposited in the trench, the trench filler material having an etch rate that is less than 1.2 times the first etch rate and substantially similar to the first etch rate (Col. 5, line 65 – Col. 6, line 3), the semiconductor structure having a planar upper surface formed of the first material and the trench filler material (Fig. 13).

The first material and the trench filler material have the same etch rate, since they are both TEOS oxides. Pan et al. do not show that the trench filler and first material have an exposed planar surface. Pan et al. teach that "it would be desirable to develop a method of forming a field isolation region with a substantially flat upper surface, without the requirement of the extra masking step required to form photoresist block…" (Col. 2, lines 42 – 45). It would have been obvious to one of ordinary skill in the art to planarize the final structure, since it is desirable to form a substantially flat upper surface.

Claim Rejections - 35 USC § 103

4. Claims 27 – 30 are rejected under 35 U.S.C. 103(a) as being unpatentable over Pan et al.

Regarding claim 27, Pan et al. teaches a semiconductor structure, wherein the first material includes silicon dioxide deposited from tetraethyorthosilicate.

Regarding claim 28, Pan et al. teaches a semiconductor structure, wherein the first material includes silicon dioxide deposited by chemical vapor deposition (Col. 4, lines 25 – 28).

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Regarding claim 29, Pan et al. teaches a semiconductor structure, wherein the first material includes silicon dioxide deposited from tetraethyorthosilicate.

Regarding claim 30, Pan et al. teaches a semiconductor structure, wherein the first material includes silicon dioxide deposited by chemical vapor deposition (Col. 5, lines 45 – 48).

Response to Arguments

5. Applicant's arguments filed June 5, 2006 have been fully considered but they are not persuasive.

Applicant argues that the deposited material is not a dielectric. It is known in the art that TEOS oxide is a dielectric.

Applicant further argues that the first material is not deposited on the support. It can be seen in Figs. 9 - 14 that the first material (44) is deposited on the support.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Douglas W. Owens whose telephone number is 571-272-1662. The examiner can normally be reached on Monday-Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Eddie C. Lee can be reached on 571-272-1732. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR.

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Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

Douglas W Owens Primary Examiner Art Unit 2811

DWO June 10, 2006